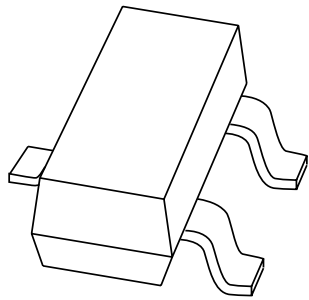


DATA SHEET



BC807

PNP general purpose transistor

Product specification
Supersedes data of 1997 Feb 28

1999 Apr 08

PNP general purpose transistor

BC807

FEATURES

- High current (max. 500 mA)
- Low voltage (max. 45 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

PNP transistor in a SOT23 plastic package.
NPN complements: BC817.

MARKING

TYPE NUMBER	MARKING CODE (1)
BC807	5D*
BC807-16	5A*
BC807-25	5B*
BC807-40	5C*

Note

1. * = p: Made in Hong Kong. * = t: Made in Malaysia.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

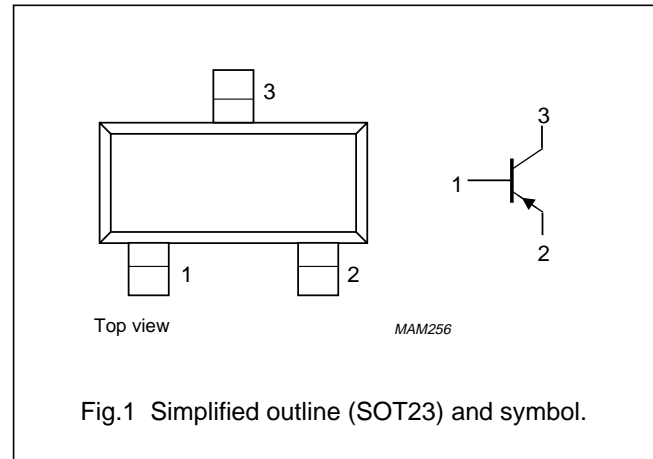
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–50	V
V_{CEO}	collector-emitter voltage	open base; $I_C = -10$ mA	–	–45	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–500	mA
I_{CM}	peak collector current		–	–1	A
I_{BM}	peak base current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



PNP general purpose transistor

BC807

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

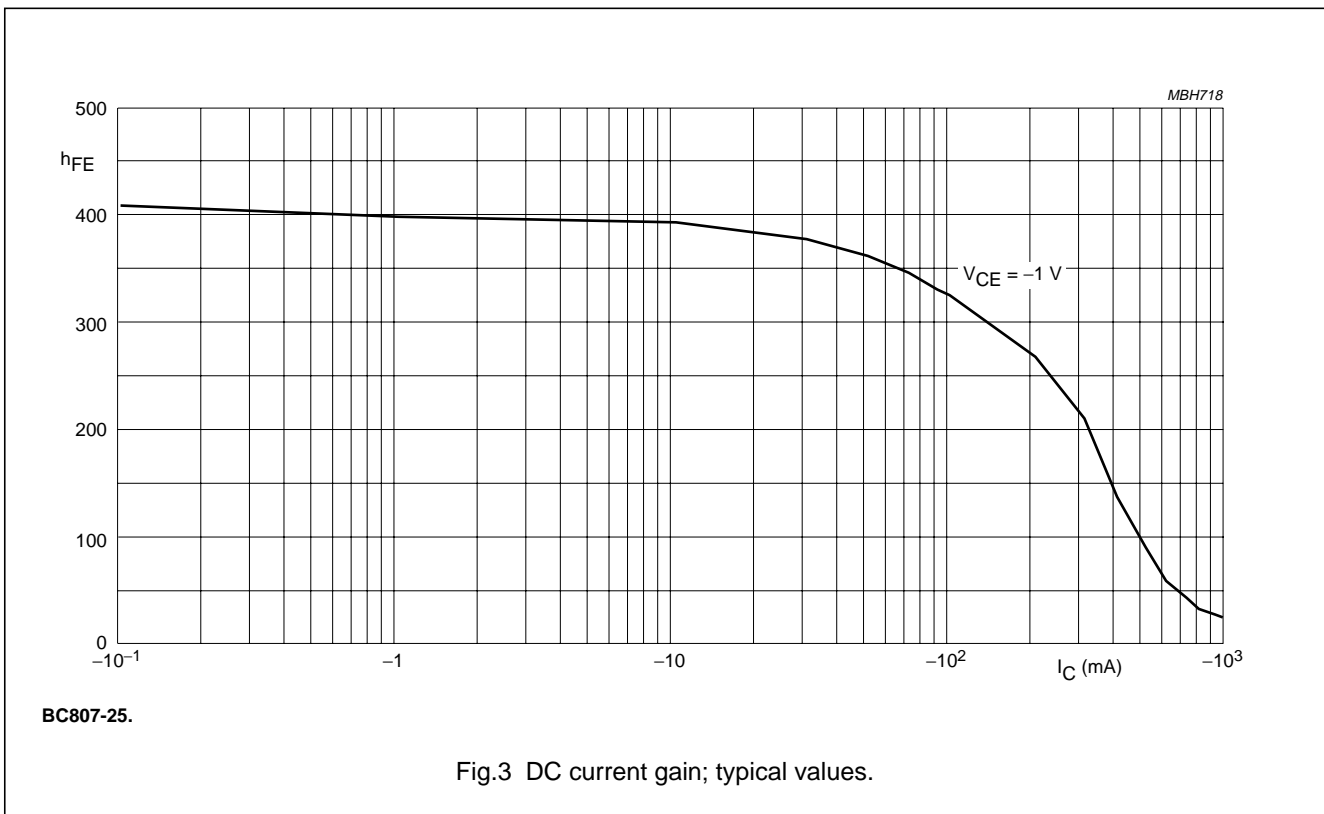
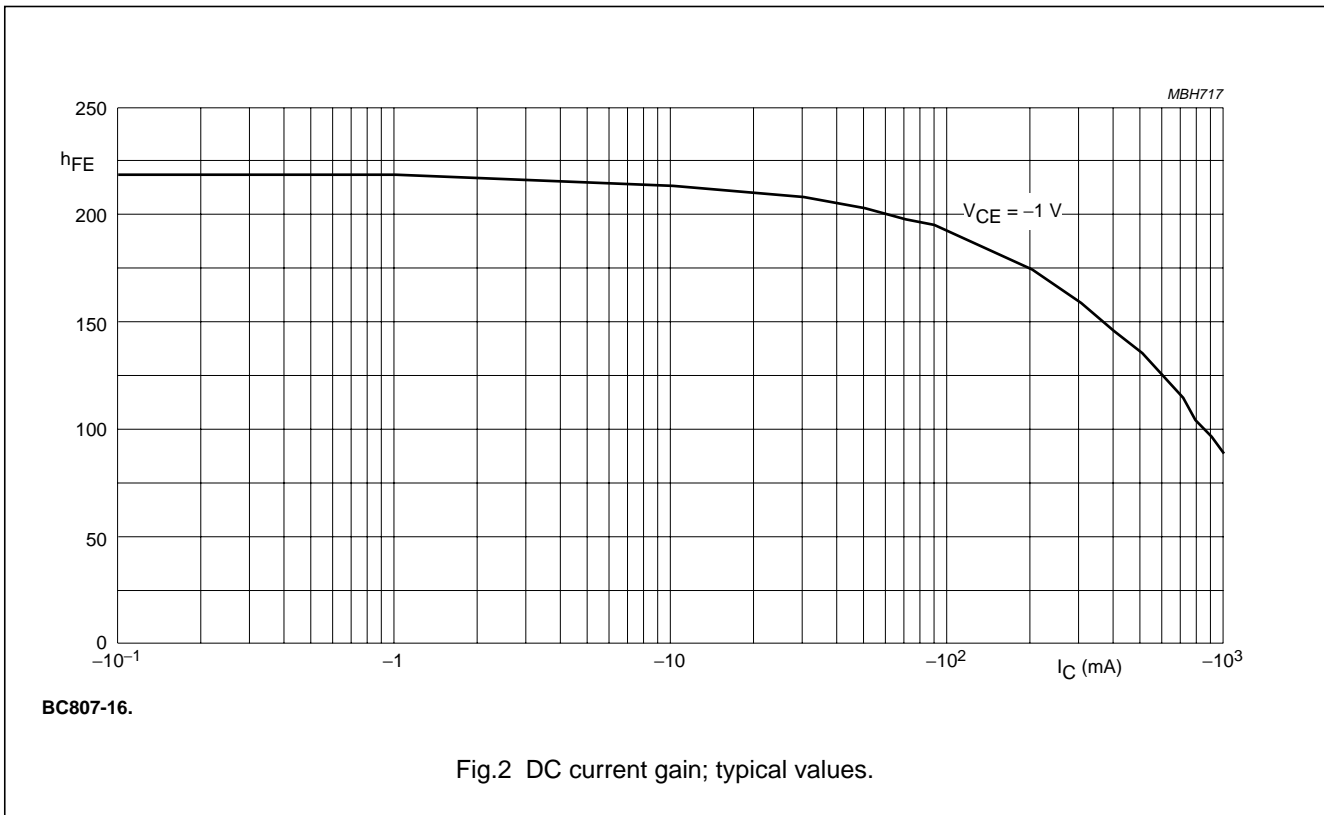
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -20\text{ V}$	–	–	–100	nA
		$I_E = 0; V_{CB} = -20\text{ V}; T_j = 150\text{ °C}$	–	–	–5	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–	–100	nA
h_{FE}	DC current gain BC807 BC807-16 BC807-25 BC807-40	$I_C = -100\text{ mA}; V_{CE} = -1\text{ V};$ note 1 see Figs 2, 3 and 4	100	–	600	
			100	–	250	
			160	–	400	
			250	–	600	
h_{FE}	DC current gain	$I_C = -500\text{ mA}; V_{CE} = -1\text{ V};$ note 1	40	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -500\text{ mA}; I_B = -50\text{ mA};$ note 1	–	–	–700	mV
V_{BE}	base-emitter voltage	$I_C = -500\text{ mA}; V_{CE} = -1\text{ V};$ notes 1 and 2	–	–	–1.2	V
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	9	–	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	80	–	–	MHz

Notes

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.
2. V_{BE} decreases by about -2 mV/K with increasing temperature.

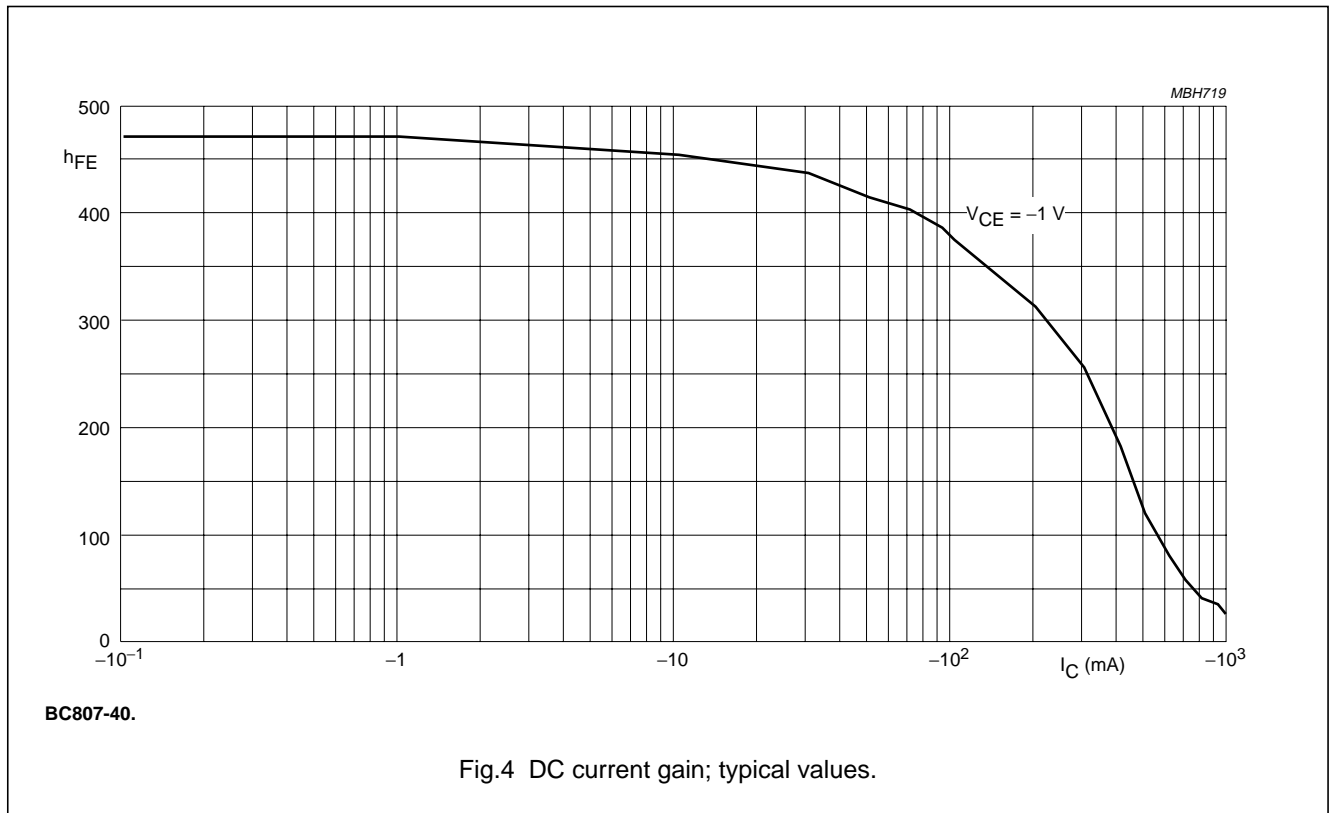
PNP general purpose transistor

BC807



PNP general purpose transistor

BC807



PNP general purpose transistor

BC807

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



BC807; BC807W; BC327

45 V, 500 mA PNP general-purpose transistors

Rev. 06 — 17 November 2009

Product data sheet

1. Product profile

1.1 General description

PNP general-purpose transistors.

Table 1. Product overview

Type number	Package		NPN complement
	NXP	JEITA	
BC807	SOT23	-	BC817
BC807W	SOT323	SC-70	BC817W
BC327 ^[1]	SOT54 (TO-92)	SC-43A	BC337

[1] Also available in SOT54A and SOT54 variant packages (see [Section 2](#)).

1.2 Features

- High current
- Low voltage

1.3 Applications

- General-purpose switching and amplification

1.4 Quick reference data

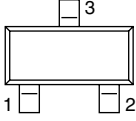
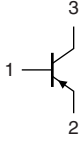
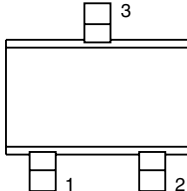
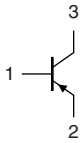
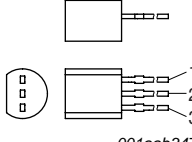
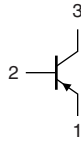
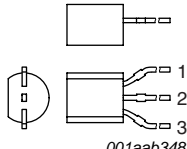
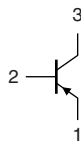
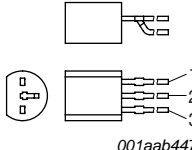
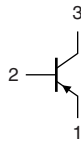
Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base; $I_C = 10 \text{ mA}$	-	-	-45	V
I_C	collector current (DC)		-	-	-500	mA
I_{CM}	peak collector current		-	-	-1	A
h_{FE}	DC current gain	$I_C = -100 \text{ mA}$; ^[1] $V_{CE} = -1 \text{ V}$				
	BC807; BC807W; BC327		100	-	600	
	BC807-16; BC807-16W; BC327-16		100	-	250	
	BC807-25; BC807-25W; BC327-25		160	-	400	
	BC807-40; BC807-40W; BC327-40		250	-	600	

[1] Pulse test: $t_p \leq 300 \mu\text{s}$; $\delta \leq 0.02$.

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
SOT23			
1	base		 sym013
2	emitter		
3	collector		
SOT323			
1	base		 sym013
2	emitter		
3	collector		
SOT54			
1	emitter		 006aaa149
2	base		
3	collector		
SOT54A			
1	emitter		 006aaa149
2	base		
3	collector		
SOT54 variant			
1	emitter		 006aaa149
2	base		
3	collector		

3. Ordering information

Table 4. Ordering information

Type number ^[1]	Package		Version
	Name	Description	
BC807	-	plastic surface mounted package; 3 leads	SOT23
BC807W	SC-70	plastic surface mounted package; 3 leads	SOT323
BC327 ^[2]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54

[1] Valid for all available selection groups.

[2] Also available in SOT54A and SOT54 variant packages (see [Section 2](#) and [Section 9](#)).

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
BC807	5D*
BC807-16	5A*
BC807-25	5B*
BC807-40	5C*
BC807W	5D*
BC807-16W	5A*
BC807-25W	5B*
BC807-40W	5C*
BC327	C327
BC327-16	C32716
BC327-25	C32725
BC327-40	C32740

[1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V_{CBO}	collector-base voltage	open emitter	-	-50	V	
V_{CEO}	collector-emitter voltage	open base; $I_C = 10$ mA	-	-45	V	
V_{EBO}	emitter-base voltage	open collector	-	-5	V	
I_C	collector current (DC)		-	-500	mA	
I_{CM}	peak collector current		-	-1	A	
I_{BM}	peak base current		-	-200	mA	
P_{tot}	total power dissipation					
	BC807	$T_{amb} \leq 25$ °C	[1][2]	-	250	mW
	BC807W	$T_{amb} \leq 25$ °C	[1][2]	-	200	mW
	BC327	$T_{amb} \leq 25$ °C	[1][2]	-	625	mW
T_{stg}	storage temperature		-65	+150	°C	
T_j	junction temperature		-	150	°C	
T_{amb}	ambient temperature		-65	+150	°C	

[1] Transistor mounted on an FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Valid for all available selection groups.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient						
	BC807	$T_{amb} \leq 25$ °C	[1][2]	-	-	500	K/W
	BC807W	$T_{amb} \leq 25$ °C	[1][2]	-	-	625	K/W
	BC327	$T_{amb} \leq 25$ °C	[1][2]	-	-	200	K/W

[1] Transistor mounted on an FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Valid for all available selection groups.

7. Characteristics

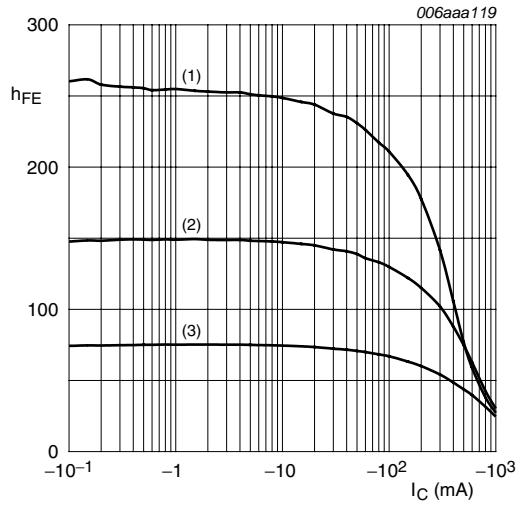
Table 8. Characteristics

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$I_E = 0\text{ A}; V_{CB} = -20\text{ V}$	-	-	-100	nA
		$I_E = 0\text{ A}; V_{CB} = -20\text{ V}; T_j = 150\text{ °C}$	-	-	-5	μA
I_{EBO}	emitter-base cut-off current	$I_C = 0\text{ A}; V_{EB} = -5\text{ V}$	-	-	-100	nA
h_{FE}	DC current gain	$I_C = -100\text{ mA}; V_{CE} = -1\text{ V}$	[1]			
		BC807; BC807W; BC327	100	-	600	
		BC807-16; BC807-16W; BC327-16	100	-	250	
		BC807-25; BC807-25W; BC327-25	160	-	400	
	BC807-40; BC807-40W; BC327-40	250	-	600		
h_{FE}	DC current gain	$I_C = -500\text{ mA}; V_{CE} = -1\text{ V}$	[1] 40	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	[1] -	-	-700	mV
V_{BE}	base-emitter voltage	$I_C = -500\text{ mA}; V_{CE} = -1\text{ V}$	[2] -	-	-1.2	V
C_c	collector capacitance	$I_E = i_e = 0\text{ A}; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	-	5	-	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	80	-	-	MHz

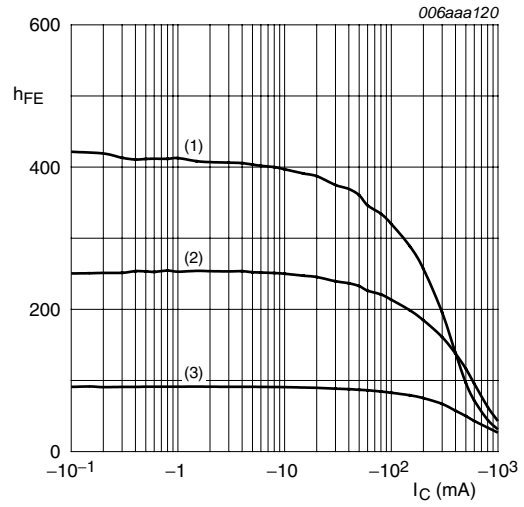
[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

[2] V_{BE} decreases by approximately 2 mV/K with increasing temperature.



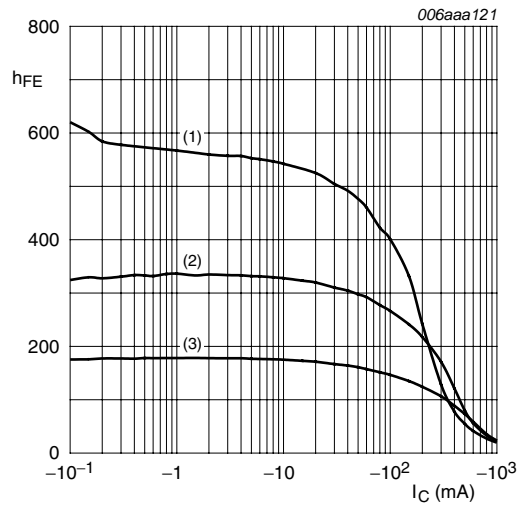
- $V_{CE} = -1\text{ V}$
- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 1. Selection -16: DC current gain as a function of collector current; typical values



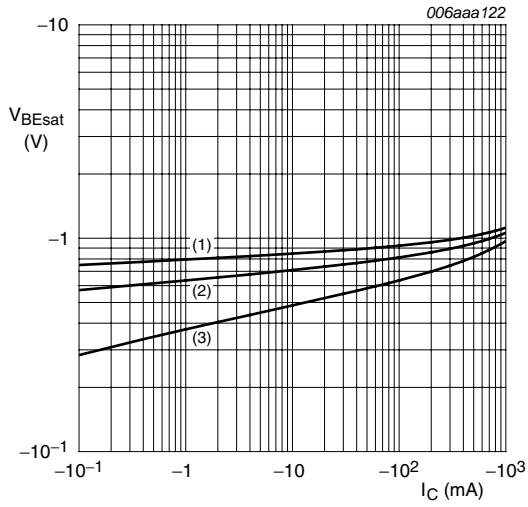
- $V_{CE} = -1\text{ V}$
- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 2. Selection -25: DC current gain as a function of collector current; typical values



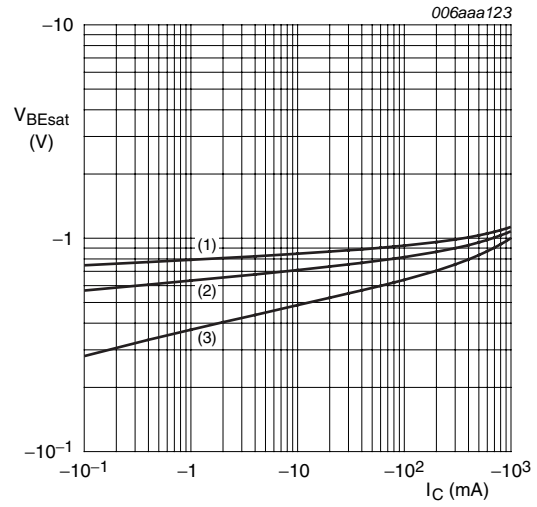
- $V_{CE} = -1\text{ V}$
- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
 - (2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
 - (3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 3. Selection -40: DC current gain as a function of collector current; typical values



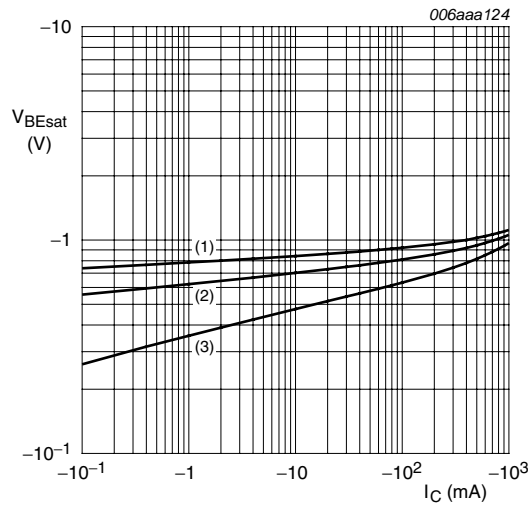
- $I_C/I_B = 10$
- (1) $T_{amb} = -55\text{ °C}$
 - (2) $T_{amb} = 25\text{ °C}$
 - (3) $T_{amb} = 150\text{ °C}$

Fig 4. Selection -16: Base-emitter saturation voltage as a function of collector current; typical values



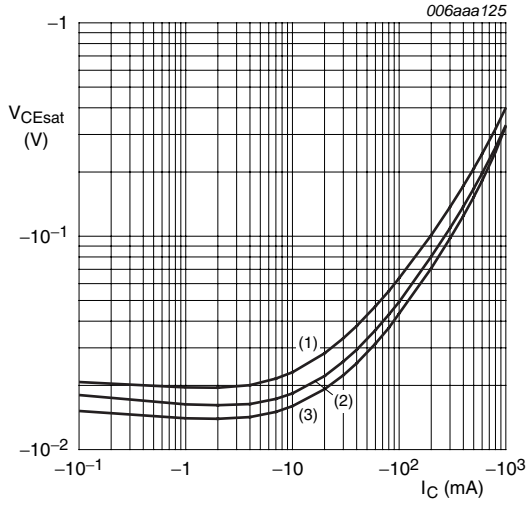
- $I_C/I_B = 10$
- (1) $T_{amb} = -55\text{ °C}$
 - (2) $T_{amb} = 25\text{ °C}$
 - (3) $T_{amb} = 150\text{ °C}$

Fig 5. Selection -25: Base-emitter saturation voltage as a function of collector current; typical values



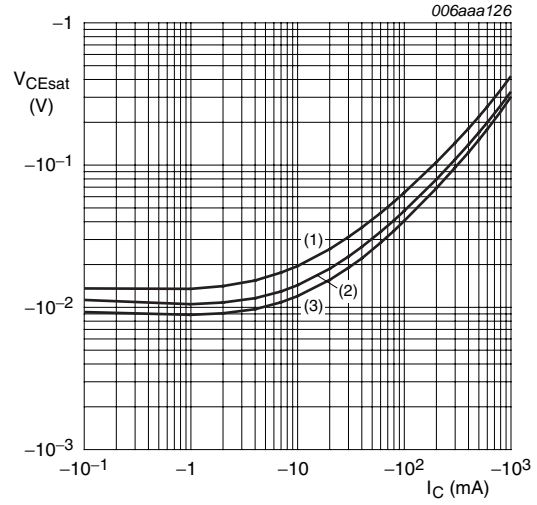
- $I_C/I_B = 10$
- (1) $T_{amb} = -55\text{ °C}$
 - (2) $T_{amb} = 25\text{ °C}$
 - (3) $T_{amb} = 150\text{ °C}$

Fig 6. Selection -40: Base-emitter saturation voltage as a function of collector current; typical values



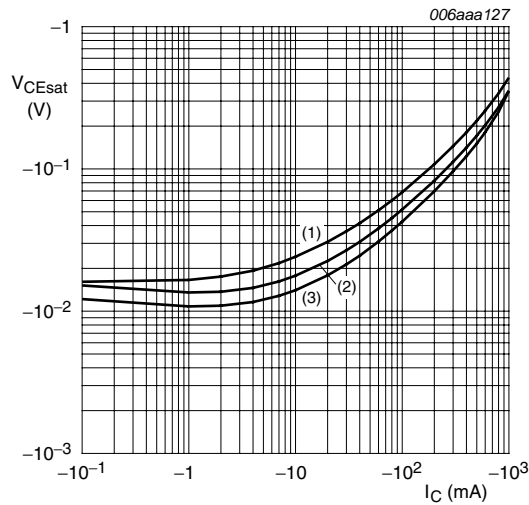
- $I_C/I_B = 10$
- (1) $T_{amb} = 150\text{ °C}$
 - (2) $T_{amb} = 25\text{ °C}$
 - (3) $T_{amb} = -55\text{ °C}$

Fig 7. Selection -16: Collector-emitter saturation voltage as a function of collector current; typical values



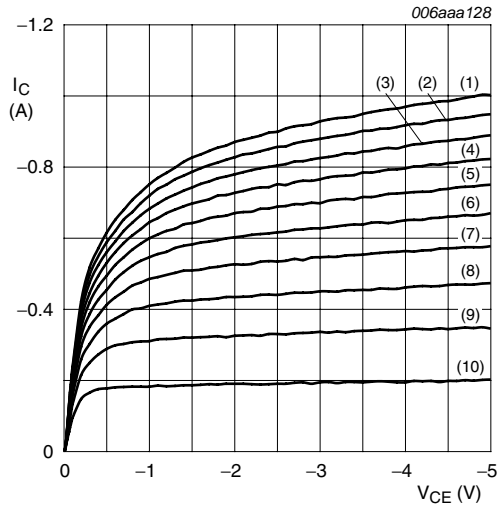
- $I_C/I_B = 10$
- (1) $T_{amb} = 150\text{ °C}$
 - (2) $T_{amb} = 25\text{ °C}$
 - (3) $T_{amb} = -55\text{ °C}$

Fig 8. Selection -25: Collector-emitter saturation voltage as a function of collector current; typical values



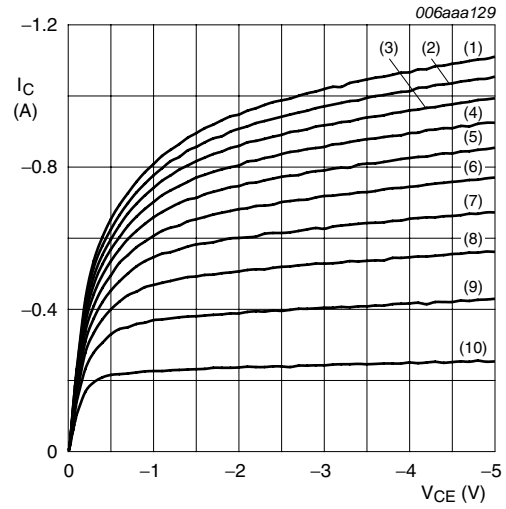
- $I_C/I_B = 10$
- (1) $T_{amb} = 150\text{ °C}$
 - (2) $T_{amb} = 25\text{ °C}$
 - (3) $T_{amb} = -55\text{ °C}$

Fig 9. Selection -40: Collector-emitter saturation voltage as a function of collector current; typical values



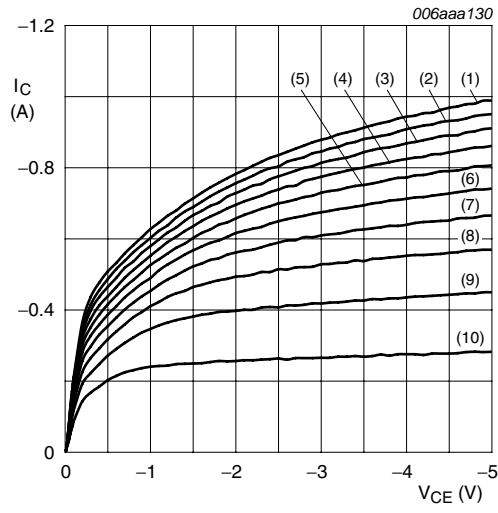
- $T_{amb} = 25\text{ }^{\circ}\text{C}$
- (1) $I_B = -16.0\text{ mA}$
 - (2) $I_B = -14.4\text{ mA}$
 - (3) $I_B = -12.8\text{ mA}$
 - (4) $I_B = -11.2\text{ mA}$
 - (5) $I_B = -9.6\text{ mA}$
 - (6) $I_B = -8.0\text{ mA}$
 - (7) $I_B = -6.4\text{ mA}$
 - (8) $I_B = -4.8\text{ mA}$
 - (9) $I_B = -3.2\text{ mA}$
 - (10) $I_B = -1.6\text{ mA}$

Fig 10. Selection -16: Collector current as a function of collector-emitter voltage; typical values



- $T_{amb} = 25\text{ }^{\circ}\text{C}$
- (1) $I_B = -13.0\text{ mA}$
 - (2) $I_B = -11.7\text{ mA}$
 - (3) $I_B = -10.4\text{ mA}$
 - (4) $I_B = -9.1\text{ mA}$
 - (5) $I_B = -7.8\text{ mA}$
 - (6) $I_B = -6.5\text{ mA}$
 - (7) $I_B = -5.2\text{ mA}$
 - (8) $I_B = -3.9\text{ mA}$
 - (9) $I_B = -2.6\text{ mA}$
 - (10) $I_B = -1.3\text{ mA}$

Fig 11. Selection -25: Collector current as a function of collector-emitter voltage; typical values



$T_{amb} = 25\text{ }^{\circ}\text{C}$

- (1) $I_B = -12.0\text{ mA}$
- (2) $I_B = -10.8\text{ mA}$
- (3) $I_B = -9.6\text{ mA}$
- (4) $I_B = -8.4\text{ mA}$
- (5) $I_B = -7.2\text{ mA}$
- (6) $I_B = -6.0\text{ mA}$
- (7) $I_B = -4.8\text{ mA}$
- (8) $I_B = -3.6\text{ mA}$
- (9) $I_B = -2.4\text{ mA}$
- (10) $I_B = -1.2\text{ mA}$

Fig 12. Selection -40: Collector current as a function of collector-emitter voltage; typical values

8. Package outline

Plastic surface-mounted package; 3 leads

SOT23

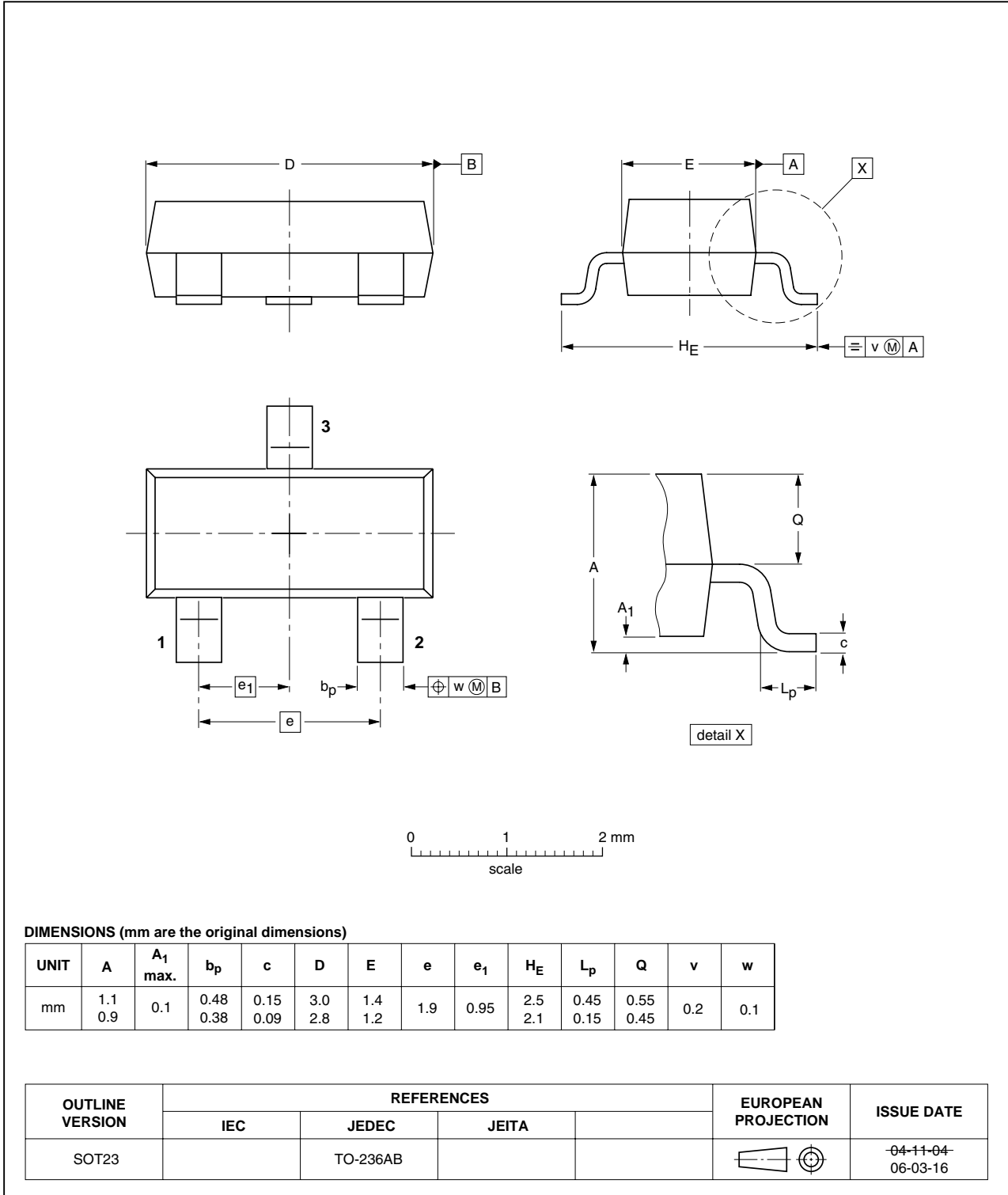


Fig 13. Package outline SOT23 (TO-236AB)

Plastic surface-mounted package; 3 leads

SOT323

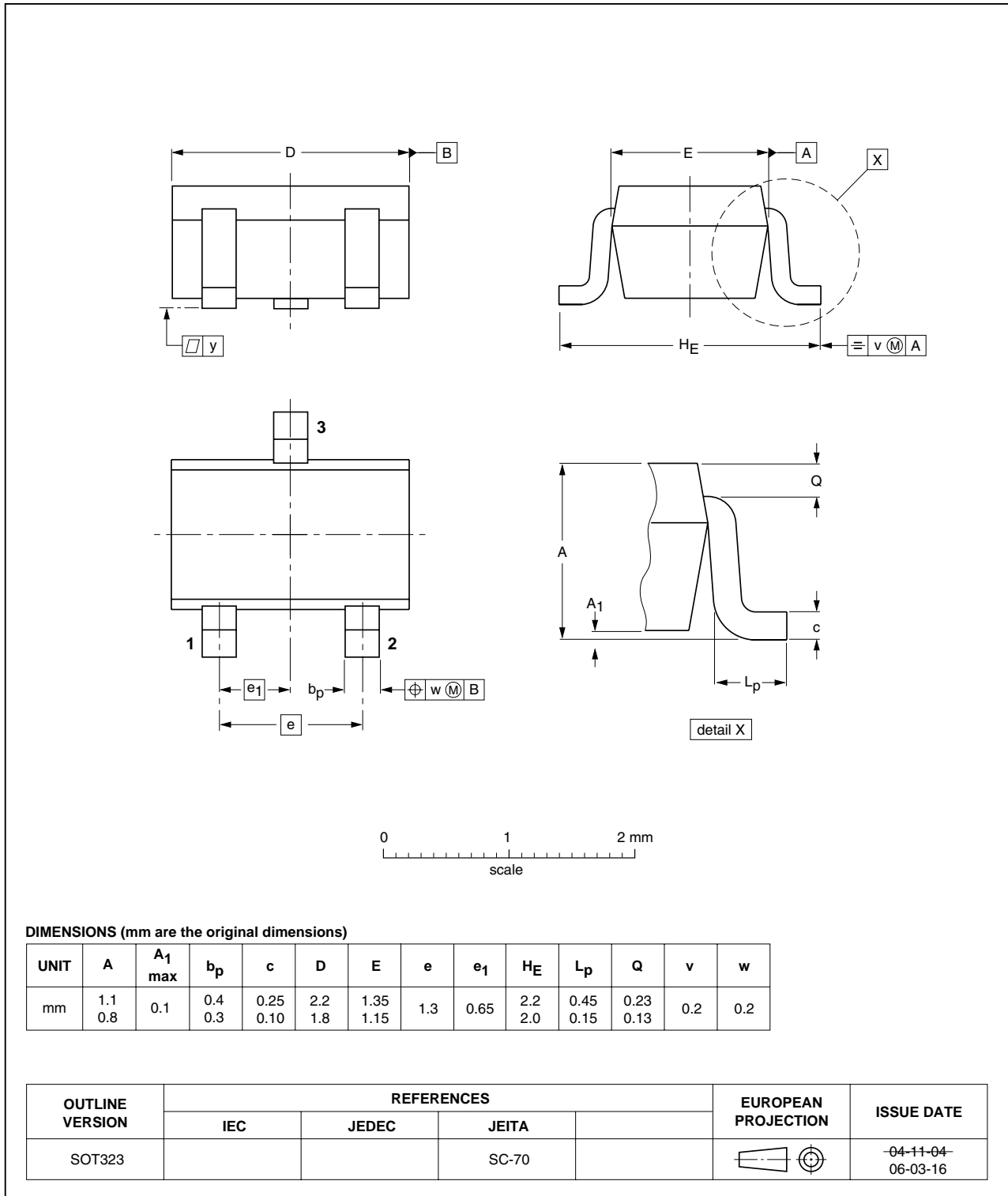


Fig 14. Package outline SOT323 (SC-70)

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

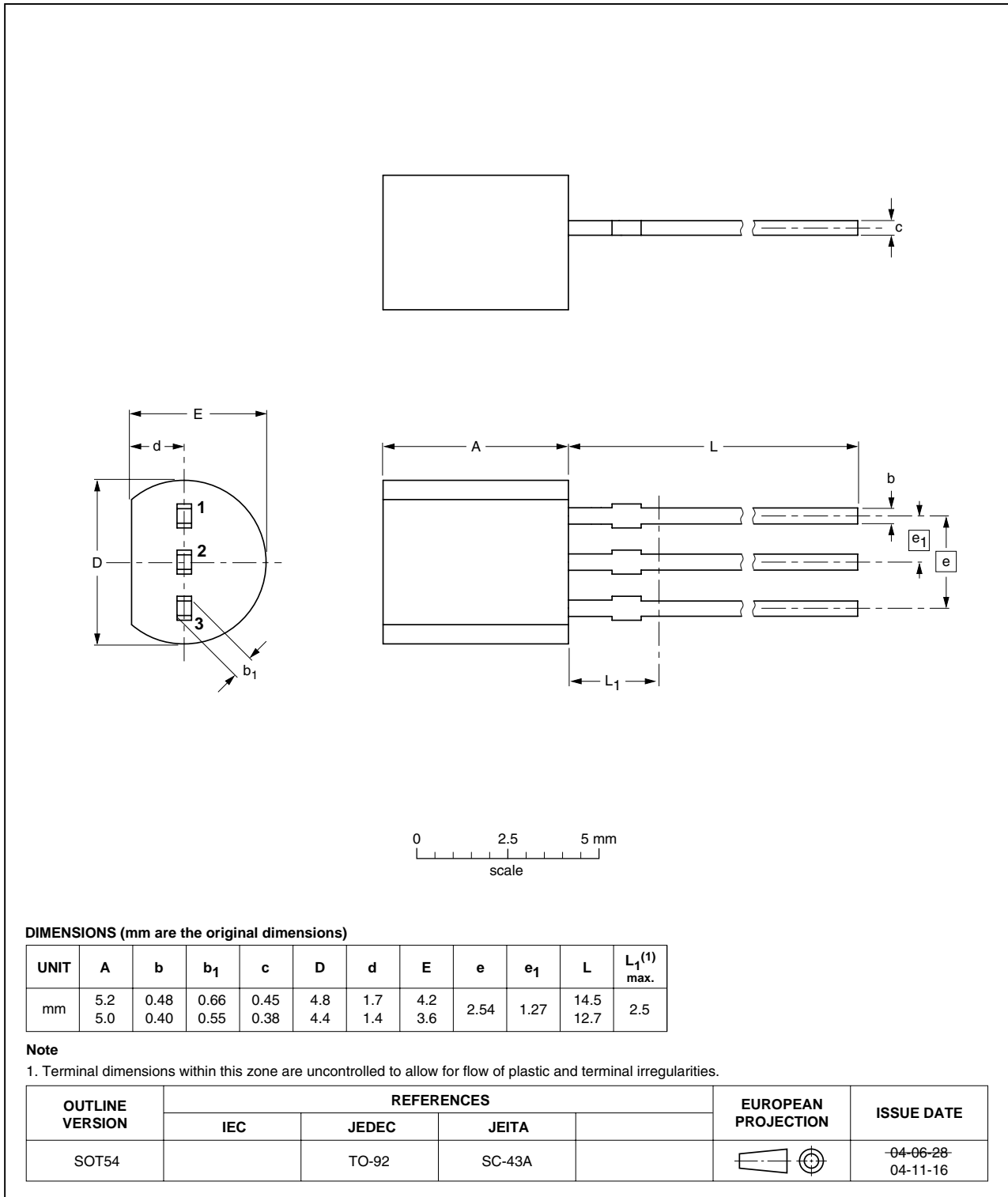


Fig 15. Package outline SOT54 (SC-43A/TO-92)

Plastic single-ended leaded (through hole) package; 3 leads (wide pitch)

SOT54A

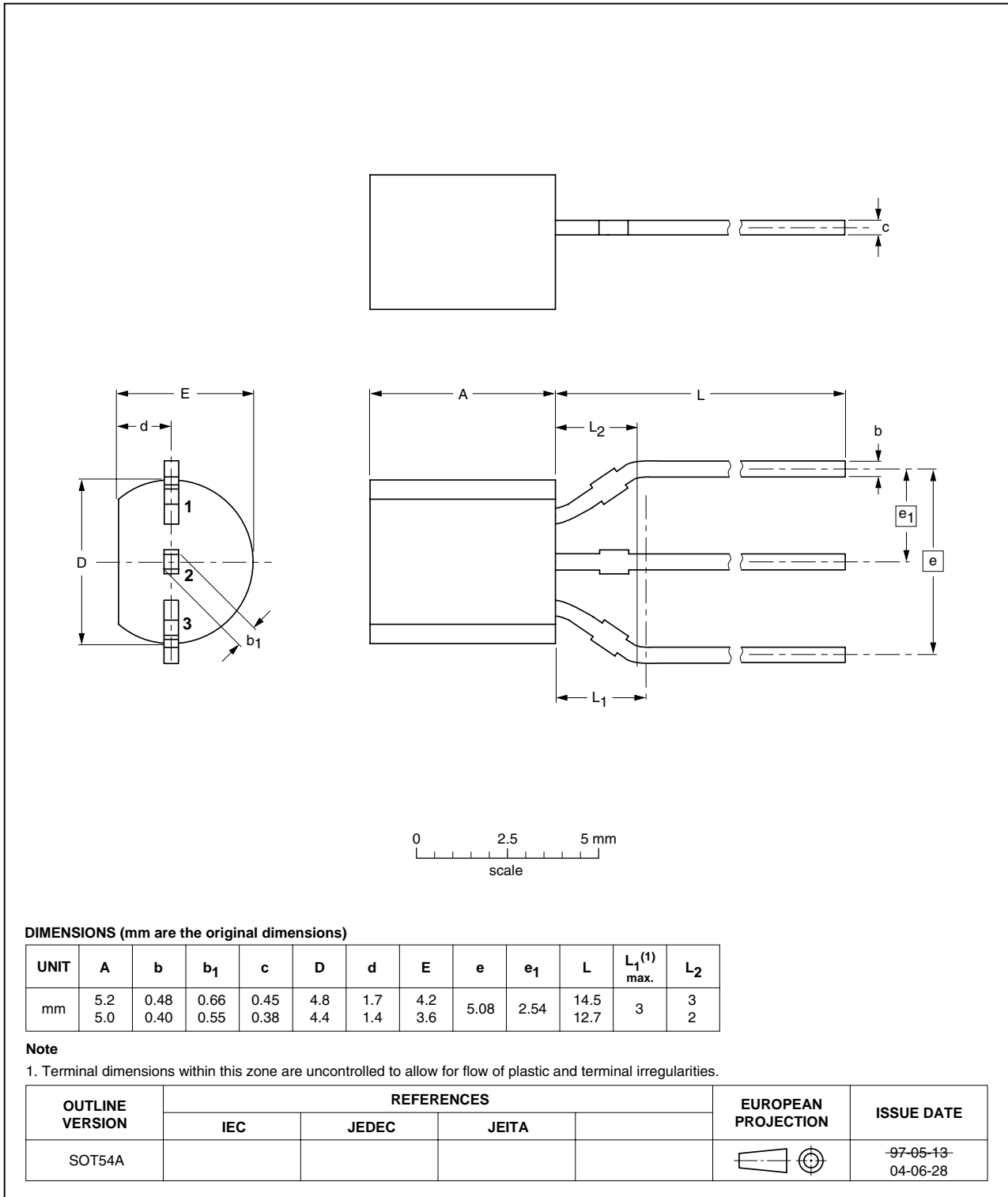


Fig 16. Package outline SOT54A

Plastic single-ended leaded (through hole) package; 3 leads (on-circle)

SOT54 variant

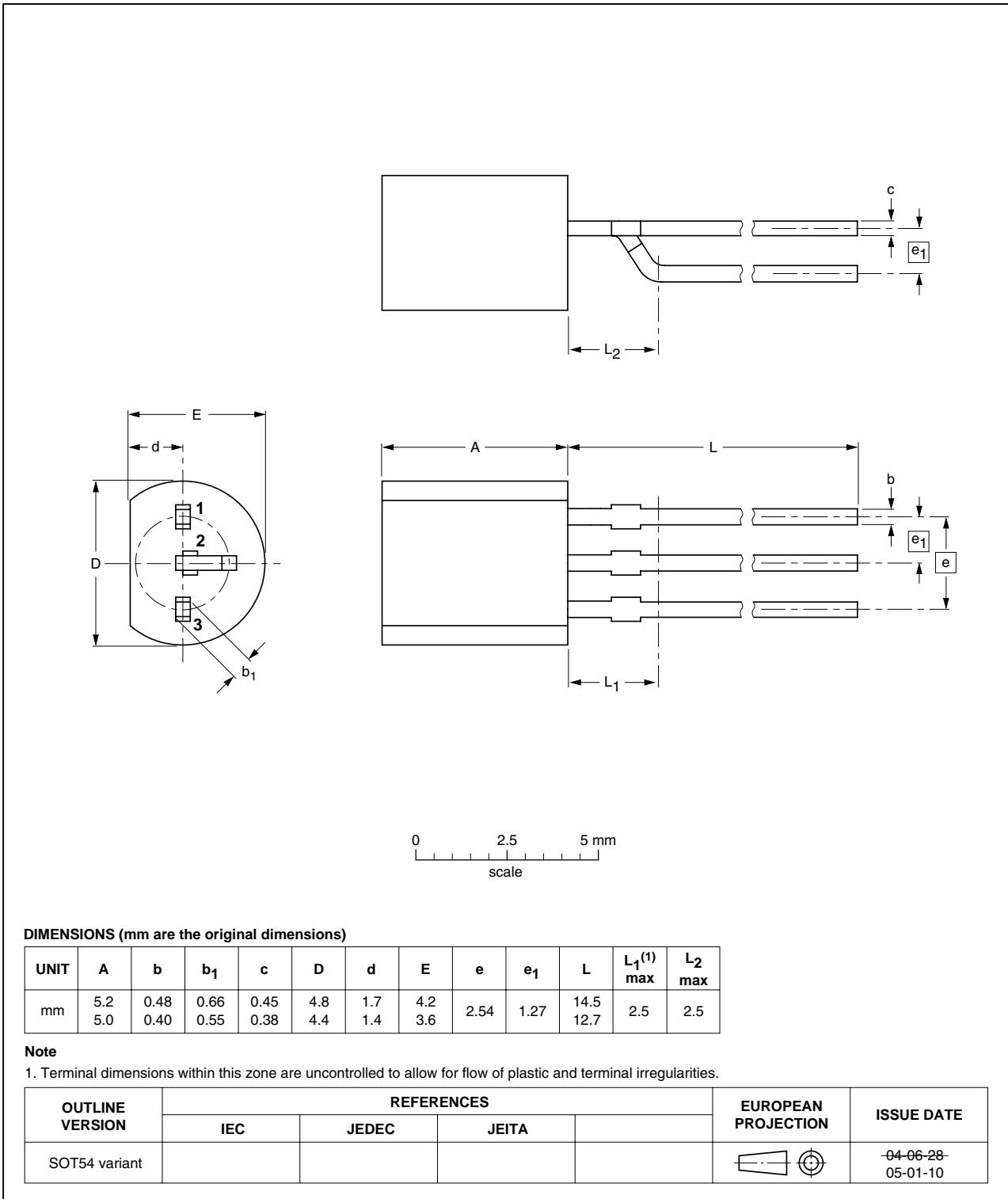


Fig 17. Package outline SOT54 variant